

Supplementary Information

Two dimensional CrGa₂Se₄: A spin-gapless ferromagnetic semiconductor with inclined uniaxial anisotropy

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Table S1 Energy difference with respect to the T-I configuration for different T and H structures.

	T-I	T-II	T-III	H-I	H-II	H-III
$\Delta E(\text{eV/f.u.})$	0	0.022	0.028	0.374	0.386	0.398

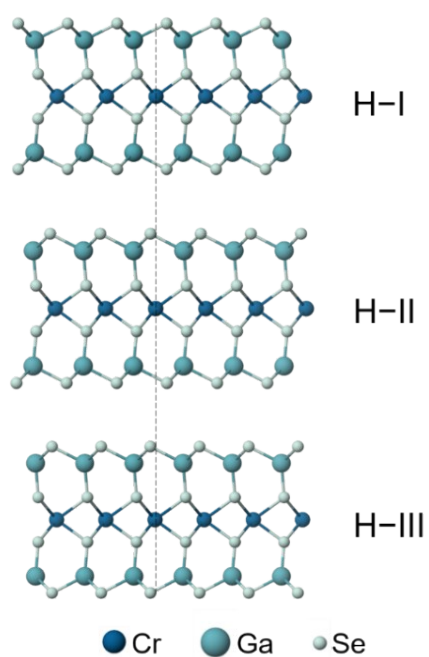


Fig. S1 Side views of three H-type configurations for CrGa₂Se₄ monolayer.

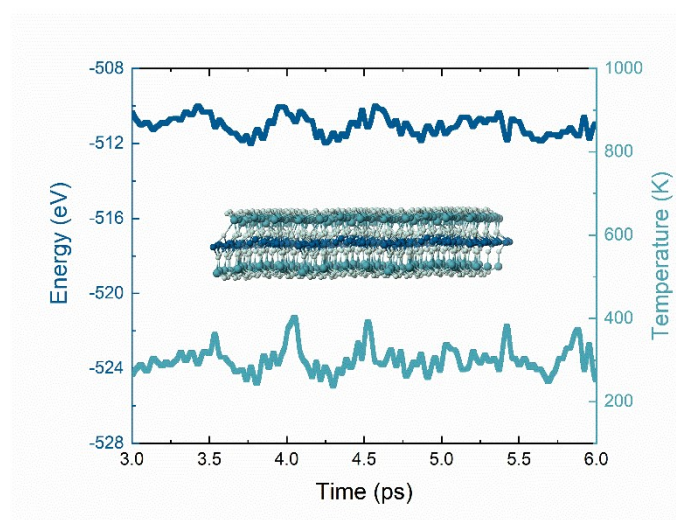


Fig. S2 AIMD evolutions of temperature and total energy of single-layer CrGa_2Se_4 and its structural snapshot at 6 ps.

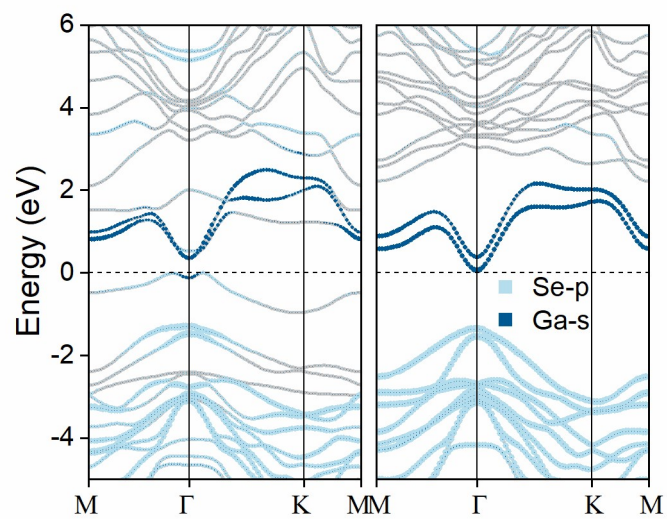


Fig. S3 Spin-polarized HSE band structure of CrGa_2Se_4 monolayer with the projection on Se-p and Ga-s orbitals.